International TOR Rectifier

Features

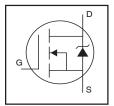
- Advanced Planar Technology
- Low On-Resistance
- Dynamic dV/dT Rating
- 150°C Operating Temperature
- Fast Switching
- · Fully Avalanche Rated
- Repetitive Avalanche Allowed up to Tjmax
- · Lead-Free, RoHS Compliant
- Automotive Qualified*

Description

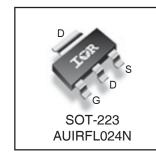
Specifically designed for Automotive applications, this cellular design of HEXFET® Power MOSFETs utilizes the latest processing techniques to achieve low onresistance per silicon area. This benefit combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in Automotive and a wide variety of other applications.



HEXFET® Power MOSFET



$V_{(BR)DSS}$	55V		
R _{DS(on)} max.		75m Ω	
I _D		2.8A	



G	D	S
Gate	Drain	Source

Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (T_A) is $25^{\circ}C$, unless otherwise specified.

	Parameter	Max.	Units
I _D @ T _A = 25°C	Continuous Drain Current, V _{GS} @ 10V ®	4.0	
I _D @ T _A = 25°C	Continuous Drain Current, V _{GS} @ 10V ^⑤	2.8	
I _D @ T _A = 70°C	Continuous Drain Current, V _{GS} @ 10V ⑤	2.3	Α
I _{DM}	Pulsed Drain Current ①	11.2	
P _D @T _A = 25°C	Power Dissipation (PCB Mount) ®	2.1	w
P _D @T _A = 25°C	Power Dissipation (PCB Mount) ®	1.0	l vv
	Linear Derating Factor (PCB Mount) ⁽⁵⁾	8.3	mW/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E _{AS}	Single Pulse Avalanche Energy (Thermally Limited) ②	214	mJ
I _{AR}	Avalanche Current ①	2.8	Α
E _{AR}	Repetitive Avalanche Energy ①⑤	0.1	mJ
dv/dt	Peak Diode Recovery dv/dt 3	5.0	V/ns
T_J	Operating Junction and	-55 to + 150	°C
T _{STG}	Storage Temperature Range		

Thermal Resistance

	111011114111100101411100							
	Parameter	Тур.	Max.	Units				
$R_{\theta JA}$	Junction-to-Ambient (PCB mount, steady state) ^⑤	90	120	°C/W				
$R_{\theta JA}$	Junction-to-Ambient (PCB mount, steady state) ®	50	60					

HEXFET® is a registered trademark of International Rectifier.

^{*}Qualification standards can be found at http://www.irf.com/

Static Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Тур.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	55			V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient		0.056		V/°C	Reference to 25°C, I _D = 1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance			75	mΩ	V _{GS} = 10V, I _D = 2.8A ⊕
V _{GS(th)}	Gate Threshold Voltage	2.0		4.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$
gfs	Forward Transconductance	3.0			S	$V_{DS} = 25V, I_D = 1.6A$
I _{DSS}	Drain-to-Source Leakage Current			25	μA	$V_{DS} = 55V, V_{GS} = 0V$
				250		$V_{DS} = 44V, V_{GS} = 0V, T_{J} = 125^{\circ}C$
I _{GSS}	Gate-to-Source Forward Leakage			100	nA	V _{GS} = 20V
	Gate-to-Source Reverse Leakage			-100		V _{GS} = -20V

Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Тур.	Max.	Units	Conditions
Q_g	Total Gate Charge			18.3		$I_D = 1.68A$
Q_{gs}	Gate-to-Source Charge			3.0	nC	$V_{DS} = 28V$
Q_{gd}	Gate-to-Drain ("Miller") Charge			7.7		V _{GS} = 10V, See Fig. 6 and 9 ⊕
t _{d(on)}	Turn-On Delay Time		8.1			$V_{DD} = 28V$
t _r	Rise Time		13.4		ns	$I_D = 1.68A$
t _{d(off)}	Turn-Off Delay Time		22.2			$R_G = 24 \Omega$
t _f	Fall Time		17.7			$R_D = 17\Omega$, See Fig. 10 ④
C _{iss}	Input Capacitance		400			$V_{GS} = 0V$
C _{oss}	Output Capacitance		145		pF	$V_{DS} = 25V$
C_{rss}	Reverse Transfer Capacitance		60			f = 1.0MHz, See Fig. 5

Diode Characteristics

	Parameter	Min.	Тур.	Max.	Units	Conditions
I _S	Continuous Source Current			2.8		MOSFET symbol
	(Body Diode)				Α	showing the
I _{SM}	Pulsed Source Current			11.2		integral reverse
	(Body Diode) ①					p-n junction diode.
V_{SD}	Diode Forward Voltage			1.0	V	$T_J = 25^{\circ}C$, $I_S = 1.68A$, $V_{GS} = 0V$ ④
t _{rr}	Reverse Recovery Time		35	53	ns	$T_J = 25$ °C, $I_F = 1.68A$
Q _{rr}	Reverse Recovery Charge		50	75	nC	di/dt = 100A/µs ⊕
t _{on}	Forward Turn-On Time	Intrinsio	turn-or	time is	negligible	e (turn-on is dominated by LS+LD)

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② V_{DD} = 25V, starting T_J = 25°C, L = 54.7mH R_G = 25 Ω , I_{AS} = 2.8A. (See Figure 12)
- 4 Pulse width $\leq 300 \mu s$; duty cycle $\leq 2\%$.
- When mounted on FR-4 board using minimum recommended footprint.
- When mounted on 1 inch square copper board, for comparison with other SMD devices.

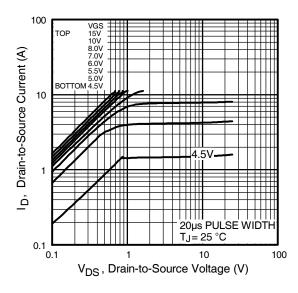
Qualification Information[†]

			Automotive				
<u> </u>		(per AEC-Q101) ^{††}					
Qualification Level		Comments: This part number(s) passed Automorqualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automorflevel.					
Moisture Sensitivity	/ Level	SOT-223 MSL1					
Machine Model Human Body Model		Class M2 (+/- 150V) ^{†††} AEC-Q101-002					
		Class H1A (+/- 350V) ^{†††} AEC-Q101-001					
	Charged Device Model	Class C5 (+/- 2000V) ^{†††} AEC-Q101-005					
RoHS Compliant	•	Yes					

[†] Qualification standards can be found at International Rectifier's web site: http://www.irf.com/

^{††} Exceptions (if any) to AEC-Q101 requirements are noted in the qualification report.

^{†††} Highest passing voltage.



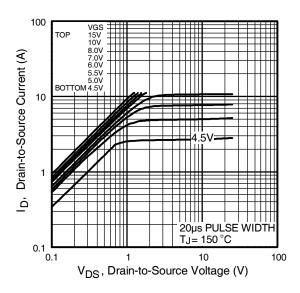
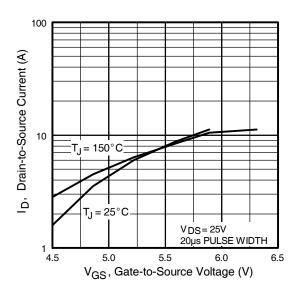


Fig 1. Typical Output Characteristics,

Fig 2. Typical Output Characteristics,



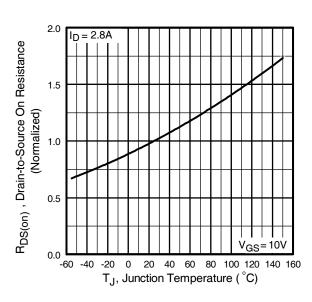
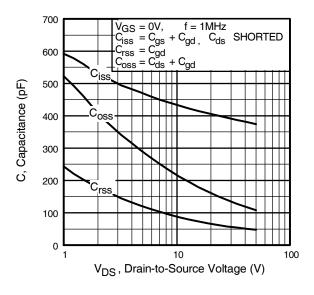


Fig 3. Typical Transfer Characteristics

Fig 4. Normalized On-Resistance Vs. Temperature



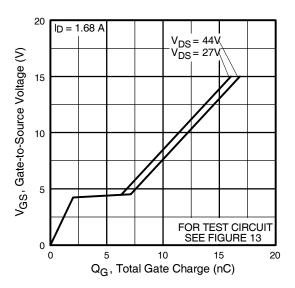
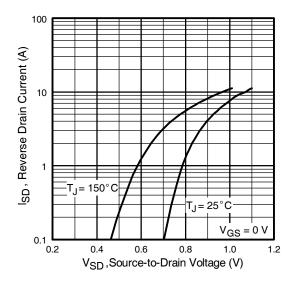


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage



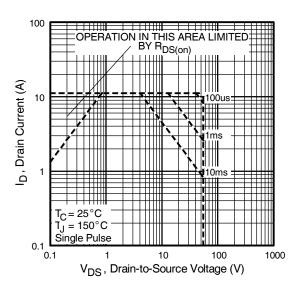


Fig 7. Typical Source-Drain Diode Forward Voltage

Fig 8. Maximum Safe Operating Area

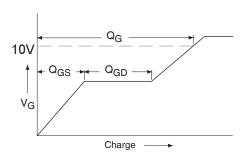
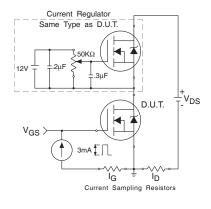


Fig 9a. Basic Gate Charge Waveform

Fig 10a. Switching Time Test Circuit



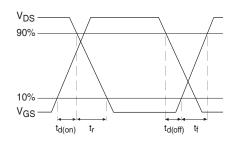


Fig 9b. Gate Charge Test Circuit

Fig 10b. Switching Time Waveforms

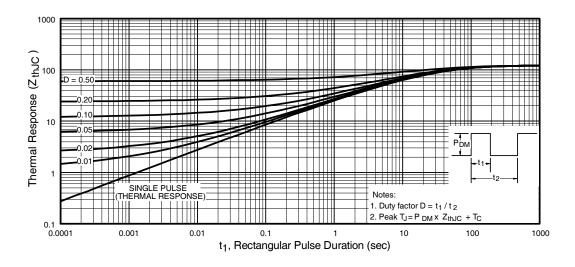


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

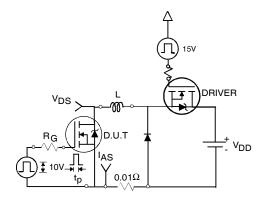
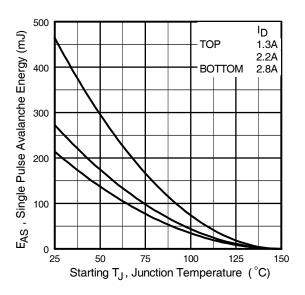


Fig 12a. Unclamped Inductive Test Circuit



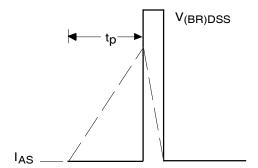
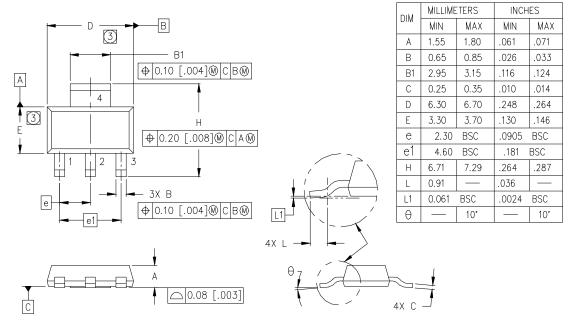


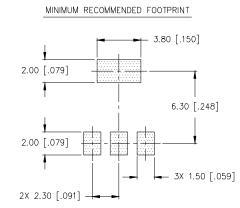
Fig 12b. Unclamped Inductive Waveforms

Fig 12c. Maximum Avalanche Energy Vs. Drain Current

SOT-223 (TO-261AA) Package Outline

Dimensions are shown in milimeters (inches)





LEAD ASSIGNMENTS

1 = GATE

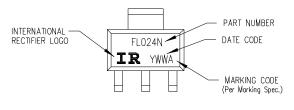
2 = DRAIN

3 = SOURCE 4 = DRAIN

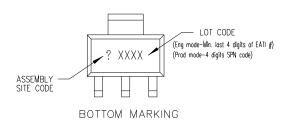
NOTES:

- 1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
- 2. CONTROLLING DIMENSION; INCH.
- (3) DIMENSIONS DO NOT INCLUDE MOLD FLASH.
- 4. OUTLINE CONFORMS TO JEDEC OUTLINE TO-261AA.
- 5. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].

SOT-223 (TO-261AA) Part Marking Information



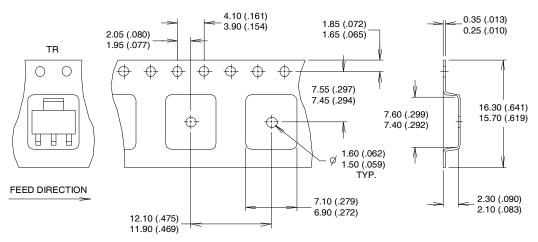
TOP MARKING



Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

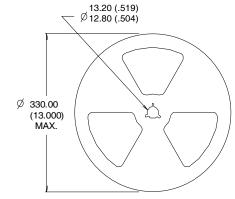
SOT-223 (TO-261AA) Tape & Reel Information

Dimensions are shown in milimeters (inches)



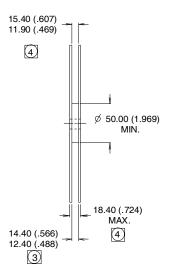
NOTES:

- 1. CONTROLLING DIMENSION: MILLIMETER.
- 2. OUTLINE CONFORMS TO EIA-481 & EIA-541. 3. EACH Ø330.00 (13.00) REEL CONTAINS 2,500 DEVICES.



NOTES:

- OUTLINE COMFORMS TO EIA-418-1.
 CONTROLLING DIMENSION HILLIMETER...
- DIMENSION MEASURED @ HUB.
- INCLUDES FLANGE DISTORTION @ OUTER EDGE.



Ordering Information

Base part number	Package Type	Standard Pack		Complete Part Number
		Form	Quantity	
AUIRFL024N	SOT-223	Tube	95	AUIRFL024N
		Tape and Reel	2500	AUIRFL024NTR

AUIRFL024N

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For technical support, please contact IR's Technical Assistance Center http://www.irf.com/technical-info/

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